Abstracts

Submicrometer Self-Aligued GaAs MESFET (Short Papers)

P. Baudet, M. Binet and D. Boccon-Gibod. "Submicrometer Self-Aligued GaAs MESFET (Short Papers)." 1976 Transactions on Microwave Theory and Techniques 24.6 (Jun. 1976 [T-MTT] (Special Issue on Microwave Field-Effect Transistors)): 372-376.

This short paper presents a self-aligned technique which permits the production of submicrometer gate lengths and spacings between contacts. The exclusive use of standard photolithographic techniques makes this method interesting. Microwave measurements are reported for such a device with a 0.7-µm gate length in a 2.2-µm drain-source spacing. The yield of the process is usually better than 80 percent.

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